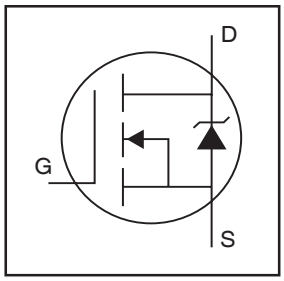
PD - 94807

International
IOR Rectifier

IRFZ34NPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Lead-Free



V_{DSS} = 55V

$R_{DS(on)}$ = 0.040Ω

I_D = 29A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	29	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	20	
I_{DM}	Pulsed Drain Current ①	100	
P_D @T_C = 25°C	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	65	mJ
I_{AR}	Avalanche Current①	16	A
E_{AR}	Repetitive Avalanche Energy①	6.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	——	2.2	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	——	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient	——	——	62	

11/3/03

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.052	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	——	——	0.040	Ω	V_{GS} = 10V, I_D = 16A④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	6.5	——	——	S	V_{DS} = 25V, I_D = 16A
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	µA	V_{DS} = 55V, V_{GS} = 0V
		——	——	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
Q_g	Total Gate Charge	——	——	34	nC	I_D = 16A
Q_{gs}	Gate-to-Source Charge	——	——	6.8		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	14		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	——	7.0	——	ns	V_{DD} = 28V
t_r	Rise Time	——	49	——		I_D = 16A
$t_{d(off)}$	Turn-Off Delay Time	——	31	——		R_G = 18Ω
t_f	Fall Time	——	40	——		R_D = 1.8Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	——	7.5	——		
C_{iss}	Input Capacitance	——	700	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	240	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	100	——		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	29	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	100		
V_{SD}	Diode Forward Voltage	——	——	1.6	V	T_J = 25°C, I_S = 16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	57	86	ns	T_J = 25°C, I_F = 16A
Q_{rr}	Reverse Recovery Charge	——	130	200	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 410µH R_G = 25Ω, I_{AS} = 16A. (See Figure 12)

③ I_{SD} ≤ 16 A, di/dt ≤ 420A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

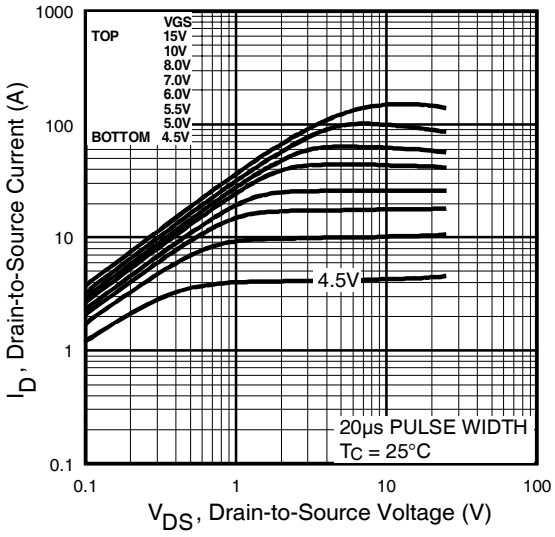


Fig 1. Typical Output Characteristics

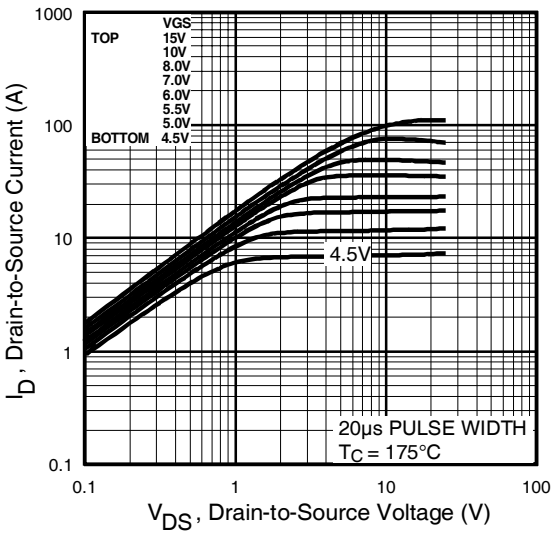


Fig 2. Typical Output Characteristics

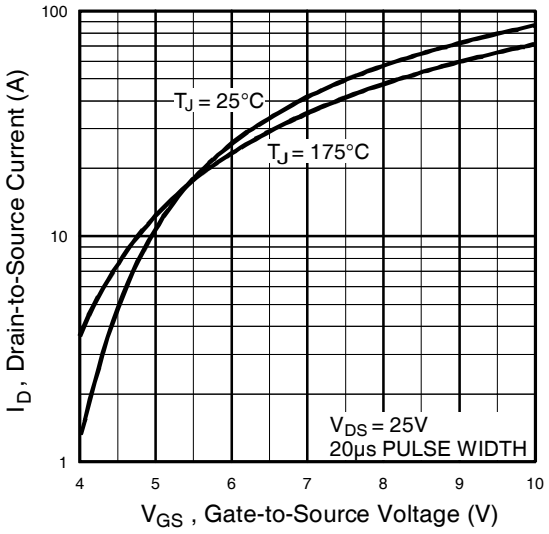


Fig 3. Typical Transfer Characteristics

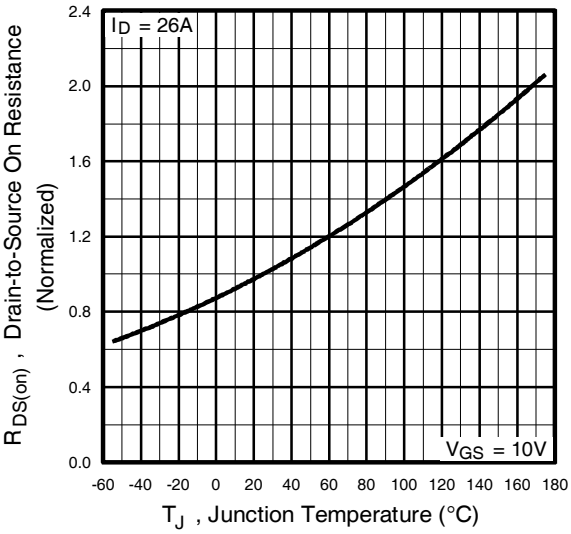


Fig 4. Normalized On-Resistance Vs. Temperature

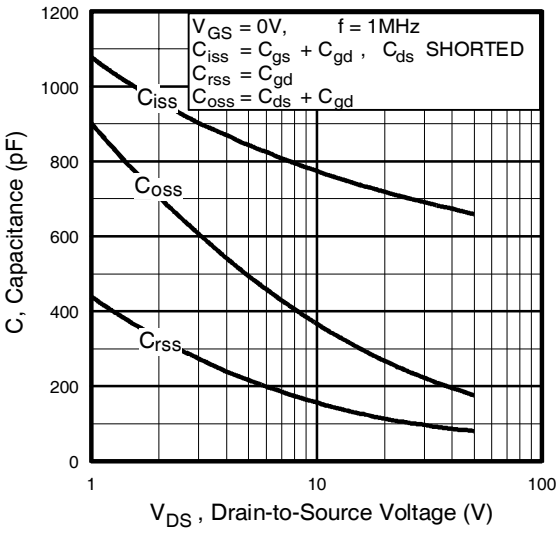


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

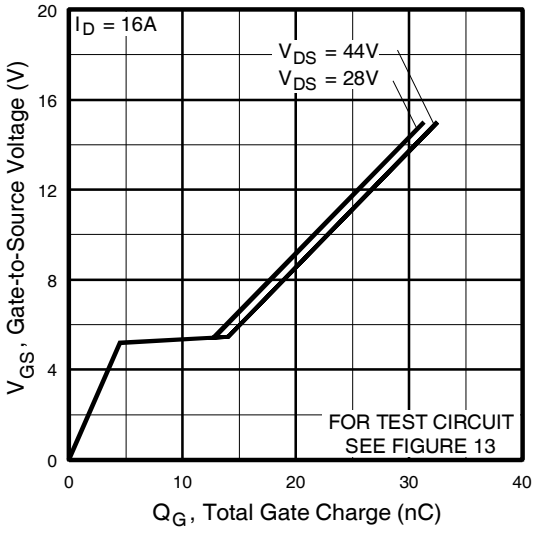


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

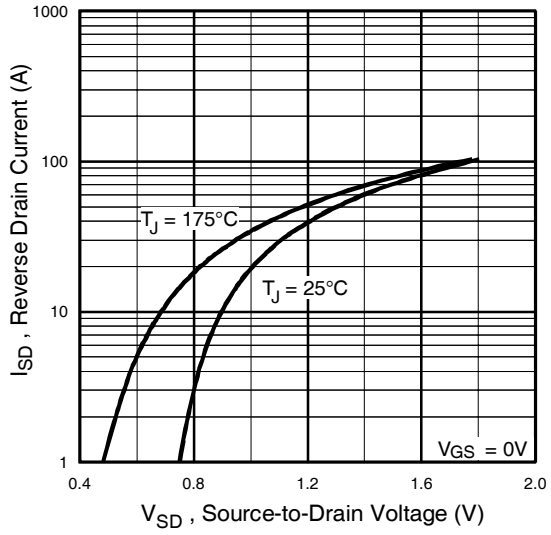


Fig 7. Typical Source-Drain Diode Forward Voltage

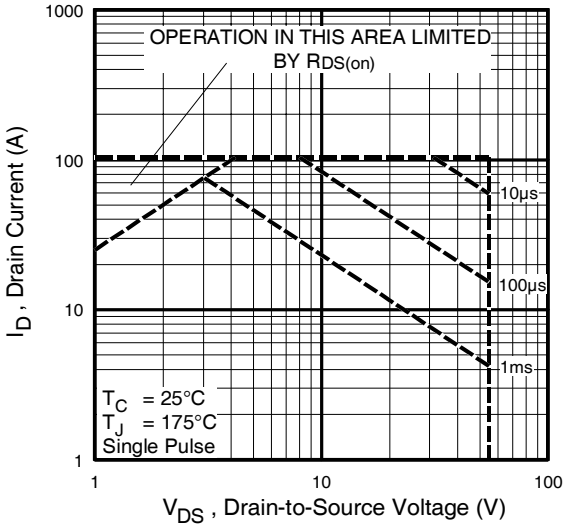


Fig 8. Maximum Safe Operating Area

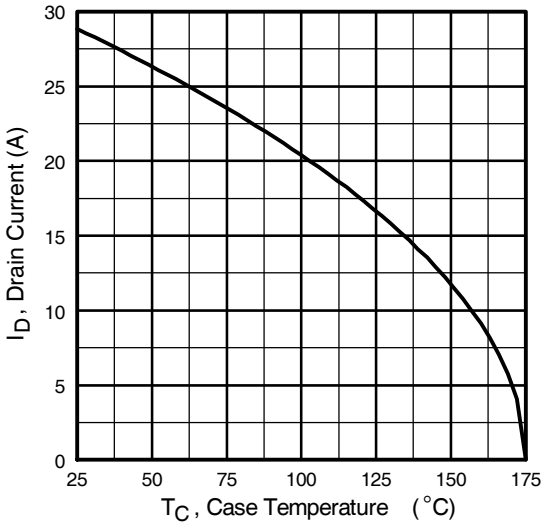


Fig 9. Maximum Drain Current Vs. Case Temperature

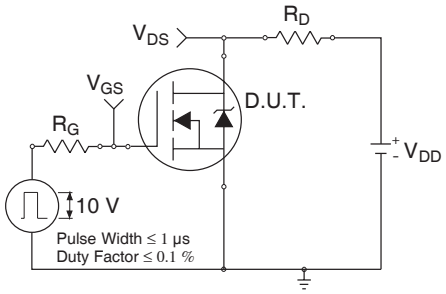


Fig 10a. Switching Time Test Circuit

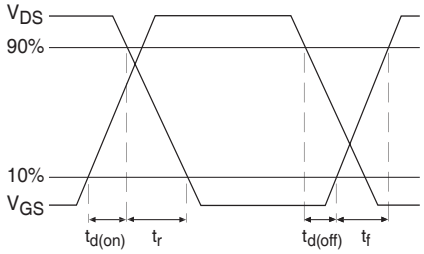


Fig 10b. Switching Time Waveforms

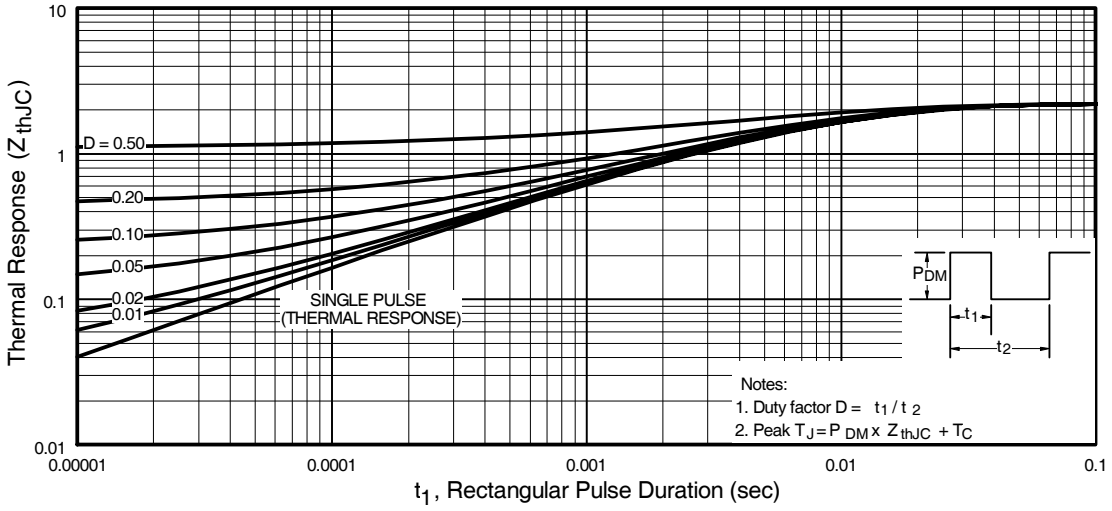


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

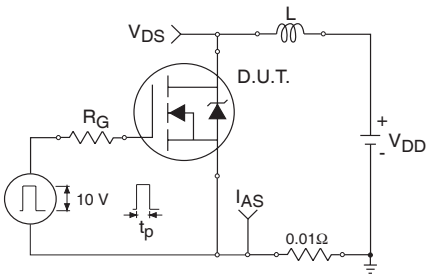


Fig 12a. Unclamped Inductive Test Circuit

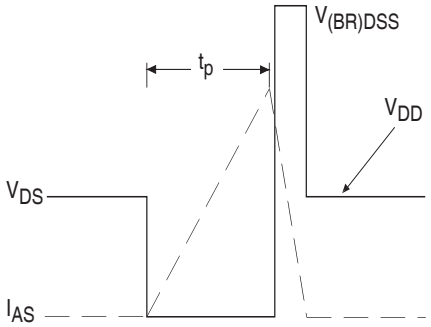


Fig 12b. Unclamped Inductive Waveforms

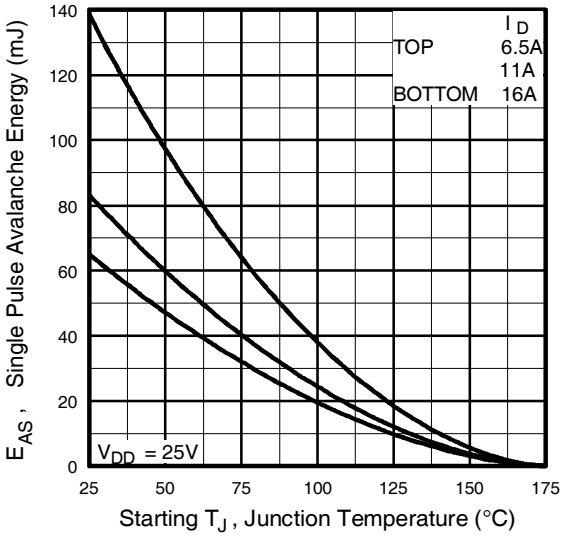


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

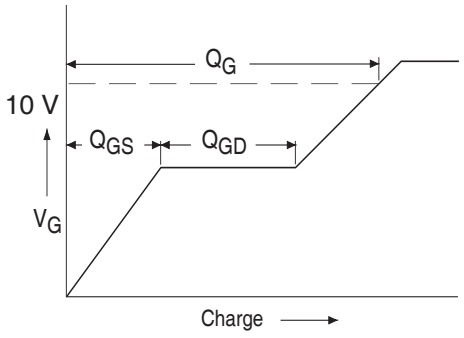


Fig 13a. Basic Gate Charge Waveform

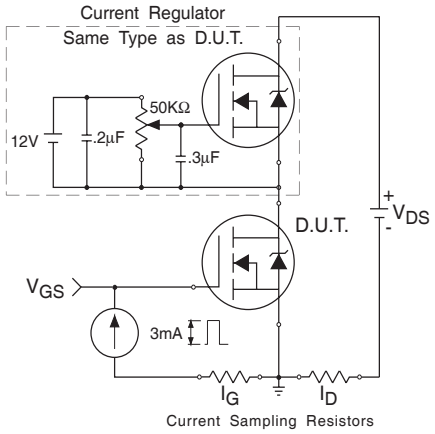
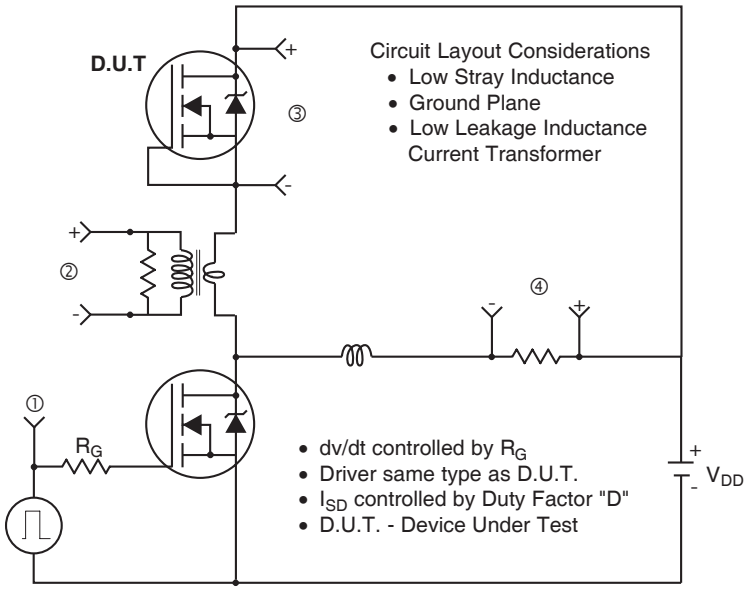
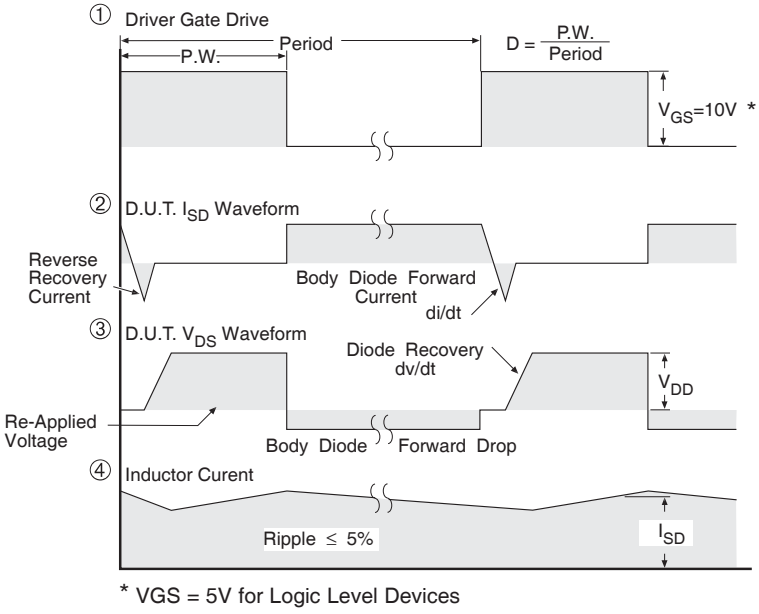


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



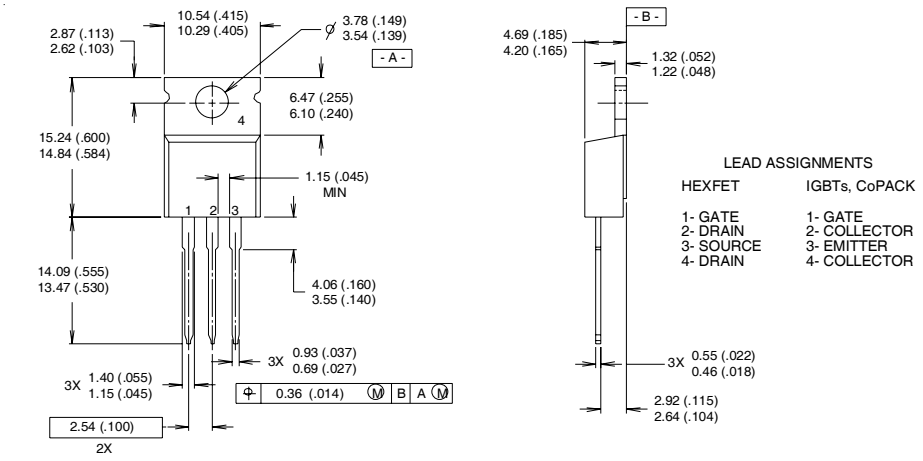


* VGS = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



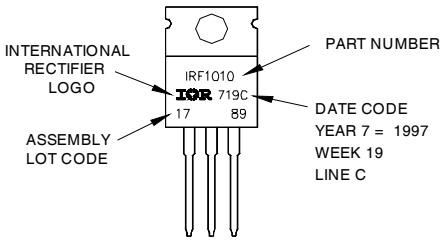
NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International
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Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/